

### **FJNS3206R**

### Switching Application (Bias Resistor Built In)

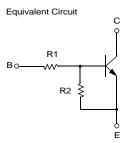
- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R<sub>1</sub>=10K $\Omega$ , R<sub>2</sub>=47K $\Omega$ )
- Complement to FJNS4206R



## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current	100	mA
P <sub>C</sub>	Collector Power Dissipation	300	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C



### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=10\mu A, I_{E}=0$	50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>B</sub> =0	50			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =40V, $I_{E}$ =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =5mA	68			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA			0.3	V
C <sub>ob</sub>	Output Capacitance	V <sub>CE</sub> =10mA, I <sub>E</sub> =0 f=1.0MHz		3.7		pF
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CB</sub> =10V, I <sub>C</sub> =5mA		250		MHz
V <sub>I</sub> (off)	Input Off Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =100μA	0.3			V
V <sub>I</sub> (on)	Input On Voltage	$V_{CE}$ =0.3V, $I_{C}$ =1mA			1.4	V
R <sub>1</sub>	Input Resistor		7	10	13	ΚΩ
R <sub>1</sub> /R <sub>2</sub>	Resistor Ratio		0.19	0.21	0.24	

# **Typical Characteristics**

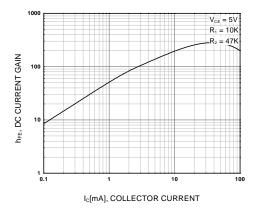


Figure 1. DC current Gain

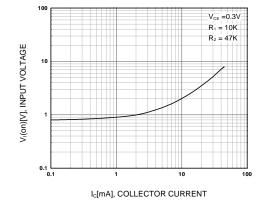


Figure 2. Input On Voltage

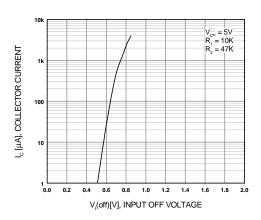


Figure 3. Input Off Voltage

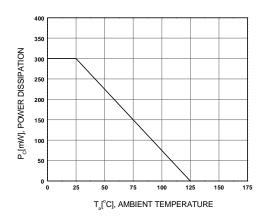
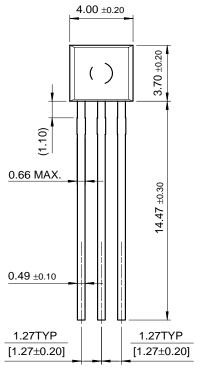
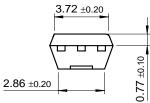
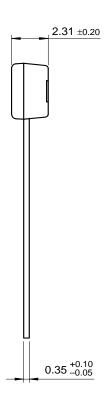


Figure 4. Power Derating

**TO-92S** 







Dimensions in Millimeters

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